FIELD EFFECT TRANSISTORS WITH VERTICAL GATE SIDE WALLS AND METHOD FOR MAKING SUCH TRANSISTORS

ABSTRACT

Metal oxide semiconductor field effect transistor (MOSFET) (20) comprising a drain region (22) and source region (24) which enclose a channel region (27). A thin gate oxide is situated on the channel region (27) and a gate conductor (23) with vettical side walls (26) is located on this gate oxide (28). The interfaces between the source region (24) and channel region (27) and the drain region (22) and channel region (27) are abrupt.

Fig 2